

# DDC (LO-R1) U

## NPN PRE-BIASED SMALL SIGNAL DUAL SURFACE MOUNT TRANSISTOR

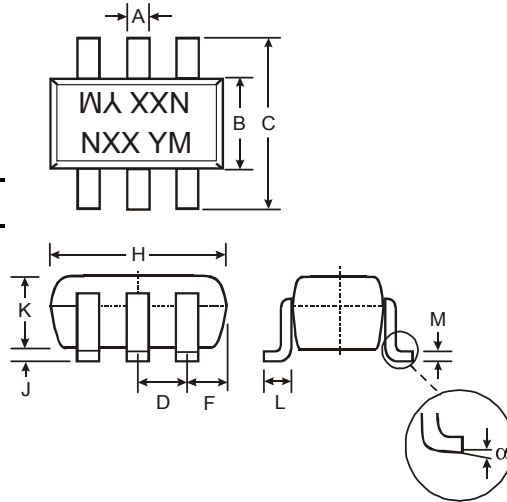
### Features

- Epitaxial Planar Die Construction
- Complementary PNP Types Available (DDA)
- Built-In Biasing Resistors
- **Lead Free/RoHS Compliant (Note 3)**
- **"Green" Device (Note 4 and 5)**

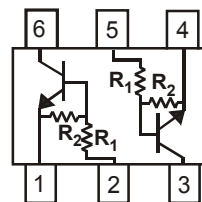
### Mechanical Data

- Case: SOT-363
- Case Material: Molded Plastic. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminals: Finish - Matte Tin Solderable per MIL-STD-202, Method 208
- Lead Free Plating (Matte Tin Finish annealed over Alloy 42 leadframe)
- Terminal Connections: See Diagram
- Marking Information: See Diagrams & Page 3
- Ordering Information: See Page 3
- Weight: 0.006 grams (approximate)

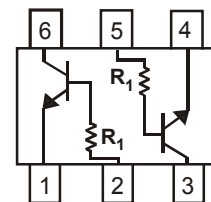
P/N	R1 (NOM)	R2 (NOM)	MARKING
DDC122LU	0.22K	10K	N81
DDC142JU	0.47K	10K	N82
DDC122TU	0.22K	OPEN	N83
DDC142TU	0.47K	OPEN	N84



SOT-363		
Dim	Min	Max
A	0.10	0.30
B	1.15	1.35
C	2.00	2.20
D	0.65 Nominal	
F	0.30	0.40
H	1.80	2.20
J	—	0.10
K	0.90	1.00
L	0.25	0.40
M	0.10	0.25
$\alpha$	0°	8°
All Dimensions in mm		



R<sub>1</sub>, R<sub>2</sub>



R<sub>1</sub> Only

SCHEMATIC DIAGRAM

### Maximum Ratings @T<sub>A</sub> = 25°C unless otherwise specified

Characteristic	Symbol	Value	Unit
Supply Voltage (6) to (1) and (3) to (4)	V <sub>CC</sub>	50	V
Input Voltage (2) to (1) and (5) to (4)	V <sub>IN</sub>	-5 to +6	V
Input Voltage (1) to (2) and (4) to (5)	V <sub>EBO</sub> (MAX)	5	V
Output Current	I <sub>C</sub>	100	mA
Power Dissipation	P <sub>d</sub>	200	mW
Thermal Resistance, Junction to Ambient Air	R <sub>θJA</sub>	625	°C/W

- Notes:
1. 150mW per element must not be exceeded.
  2. Mounted on FR4 PC Board with recommended pad layout at <http://www.diodes.com/datasheets/ap02001.pdf>.
  3. No purposefully added lead.
  4. Diodes Inc.'s "Green" policy can be found on our website at [http://www.diodes.com/products/lead\\_free/index.php](http://www.diodes.com/products/lead_free/index.php).
  5. Product manufactured with Date Code UO (week 40, 2007) and newer are built with Green Molding Compound. Product manufactured prior to Date Code UO are built with Non-Green Molding Compound and may contain Halogens or Sb2O3 Fire Retardants.

## Electrical Characteristics

@T<sub>A</sub> = 25°C unless otherwise specified

## R1, R2 Types

Characteristic		Symbol	Min	Typ	Max	Unit	Test Condition
Input Voltage	DDC122LU DDC142JU	V <sub>I(off)</sub>	0.3 0.3	—	—	V	V <sub>CC</sub> = 5V, I <sub>O</sub> = 100μA
	DDC122LU DDC142JU	V <sub>I(on)</sub>	—	—	2.0 2.0	V	V <sub>O</sub> = 0.3V, I <sub>O</sub> = 20mA V <sub>O</sub> = 0.3V, I <sub>O</sub> = 20mA
Output Voltage		V <sub>O(on)</sub>	—	—	0.3V	V	I <sub>O</sub> /I <sub>I</sub> = 5mA/0.25mA
Input Current	DDC122LU DDC142JU	I <sub>I</sub>	—	—	28 13	mA	V <sub>I</sub> = 5V
Output Current		I <sub>O(off)</sub>	—	—	0.5	μA	V <sub>CC</sub> = 50V, V <sub>I</sub> = 0V
DC Current Gain	DDC122LU DDC142JU	G <sub>I</sub>	56 56	—	—	—	V <sub>O</sub> = 5V, I <sub>O</sub> = 10mA
Gain-Bandwidth Product*		f <sub>T</sub>	—	200	—	MHz	V <sub>CE</sub> = 10V, I <sub>E</sub> = 5mA, f = 100MHz

\* Transistor - For Reference Only

## Electrical Characteristics

@T<sub>A</sub> = 25°C unless otherwise specified

## R1- Only

Characteristic		Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage		BV <sub>CBO</sub>	50	—	—	V	I <sub>C</sub> = 50μA
Collector-Emitter Breakdown Voltage		BV <sub>CEO</sub>	40	—	—	V	I <sub>C</sub> = 1mA
Emitter-Base Breakdown Voltage	DDC122TU DDC142TU	BV <sub>EBO</sub>	5	—	—	V	I <sub>E</sub> = 50μA I <sub>E</sub> = 50μA
Collector Cutoff Current		I <sub>CBO</sub>	—	—	0.5	μA	V <sub>CB</sub> = 50V
Emitter Cutoff Current	DDC122TU DDC142TU	I <sub>EBO</sub>	— —	—	0.5 0.5	μA	V <sub>EB</sub> = 4V
Collector-Emitter Saturation Voltage		V <sub>CE(sat)</sub>	—	—	0.3	V	I <sub>C</sub> = 5mA, I <sub>B</sub> = 0.25mA
DC Current Transfer Ratio	DDC122TU DDC142TU	h <sub>FE</sub>	100 100	250 250	600 600	—	I <sub>C</sub> = 1mA, V <sub>CE</sub> = 5V
Gain-Bandwidth Product*		f <sub>T</sub>	—	200	—	MHz	V <sub>CE</sub> = 10V, I <sub>E</sub> = -5mA, f = 100MHz

\* Transistor - For Reference Only

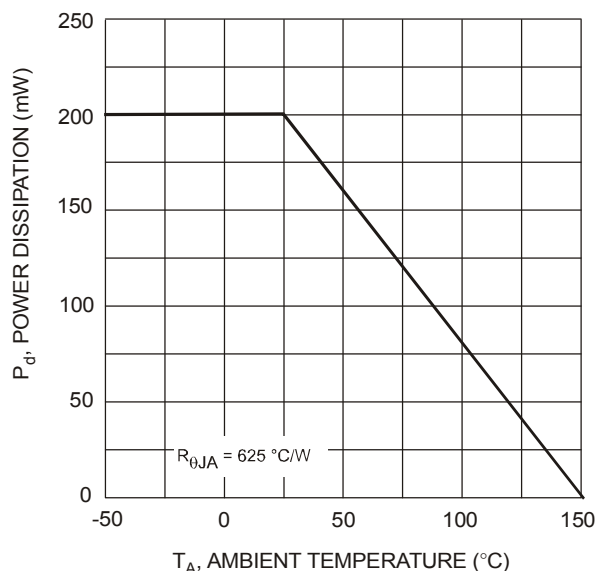


Fig. 1 Power Derating Curve

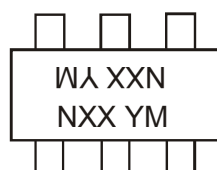
(150mW per element must not be exceeded).

## Ordering Information (Note 6)

Device	Packaging	Shipping
DDC122LU-7-F	SOT-363	3000/Tape & Reel
DDC142JU-7-F	SOT-363	3000/Tape & Reel
DDC122TU-7-F	SOT-363	3000/Tape & Reel
DDC142TU-7-F	SOT-363	3000/Tape & Reel

Notes: 6. For packaging details, go to our website at <http://www.diodes.com/datasheets/ap02007.pdf>.

## Marking Information



NXX = Product Type Marking Code  
See Page 1 Diagrams  
YM = Date Code Marking  
Y = Year ex: T = 2006  
M = Month ex: 9 = September

### Date Code Key

Year	2002	2003	2004	2005	2006	2007	2008	2009	2010	2011	2012
Code	N	P	R	S	T	U	V	W	X	Y	Z

Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	O	N	D

### IMPORTANT NOTICE

Diodes Incorporated and its subsidiaries reserve the right to make modifications, enhancements, improvements, corrections or other changes without further notice to any product herein. Diodes Incorporated does not assume any liability arising out of the application or use of any product described herein; neither does it convey any license under its patent rights, nor the rights of others. The user of products in such applications shall assume all risks of such use and will agree to hold Diodes Incorporated and all the companies whose products are represented on our website, harmless against all damages.

### LIFE SUPPORT

Diodes Incorporated products are not authorized for use as critical components in life support devices or systems without the expressed written approval of the President of Diodes Incorporated.